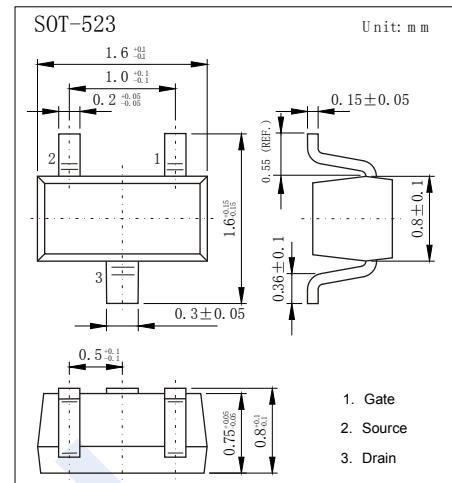
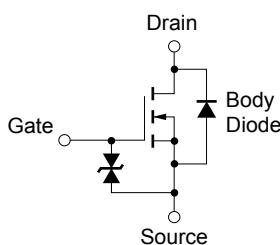


N-Channel MOSFET

2SK3503

■ Features

- $V_{DS} (V) = 16V$
- $I_D = 100 \text{ mA } (V_{GS} = 1.5V)$
- $R_{DS(ON)} < 50 \Omega \text{ } (V_{GS} = 1.5V)$
- $R_{DS(ON)} < 15 \Omega \text{ } (V_{GS} = 2.5V)$
- $R_{DS(ON)} < 12 \Omega \text{ } (V_{GS} = 4V)$



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	16	V
Gate-Source Voltage	V_{GS}	± 7	
Continuous Drain Current $T_c=25^\circ\text{C}$	I_D	100	mA
Pulsed Drain Current (Note.1)	I_{DM}	400	
Power Dissipation $T_c=25^\circ\text{C}$	P_D	200	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	

Note.1: $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D=250 \mu\text{A}, V_{GS}=0\text{V}$	16			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=16\text{V}, V_{GS}=0\text{V}$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS}=0\text{V}, V_{GS}=\pm 7\text{V}$			± 3	
Gate Cut-off Voltage	$V_{GS(off)}$	$V_{DS}=3\text{V}, I_D=10 \mu\text{A}$	0.5	0.8	1.1	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=1.5\text{V}, I_D=1 \text{mA}$		20	50	Ω
		$V_{GS}=2.5\text{V}, I_D=10 \text{mA}$		7	15	
		$V_{GS}=4\text{V}, I_D=10 \text{mA}$		5	12	
Forward Transconductance	g_{FS}	$V_{DS}=3\text{V}, I_D=10 \text{mA}$	20			mS
Input Capacitance	C_{iss}	$V_{GS}=0\text{V}, V_{DS}=3\text{V}, f=1\text{MHz}$		10		pF
Output Capacitance	C_{oss}			13		
Reverse Transfer Capacitance	C_{rss}			3		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=3\text{V}, V_{DS}=3\text{V}, I_D=10\text{mA}, R_G=10 \Omega$		15		ns
Turn-On Rise Time	t_r			70		
Turn-Off Delay Time	$t_{d(off)}$			100		
Turn-Off Fall Time	t_f			110		

■ Marking

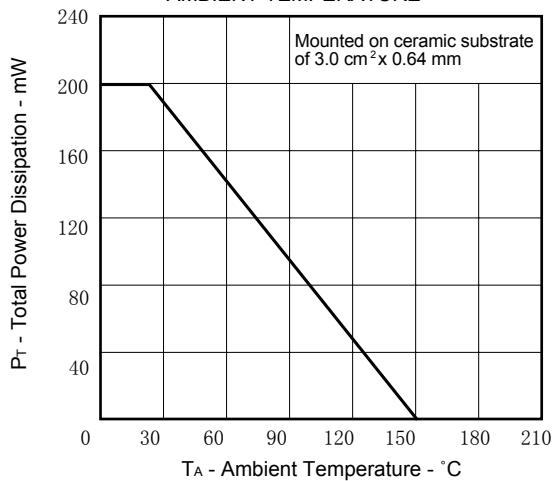
Marking	E1
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N-Channel MOSFET

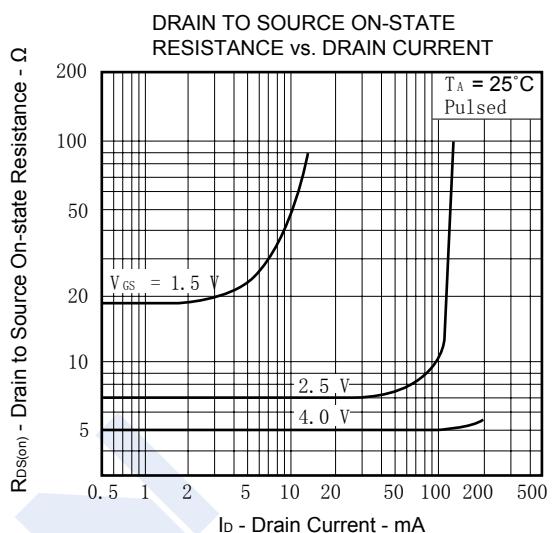
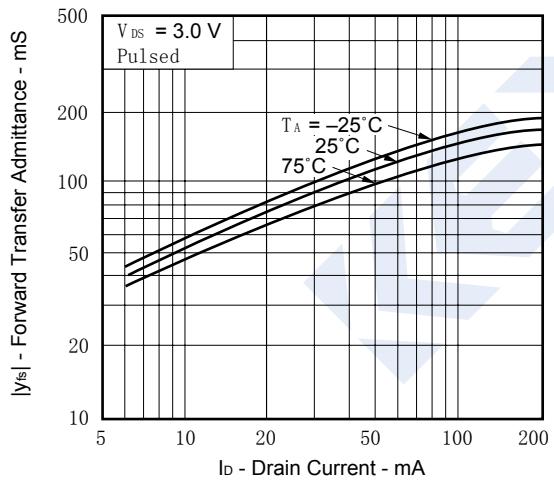
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■ Typical Characteristics

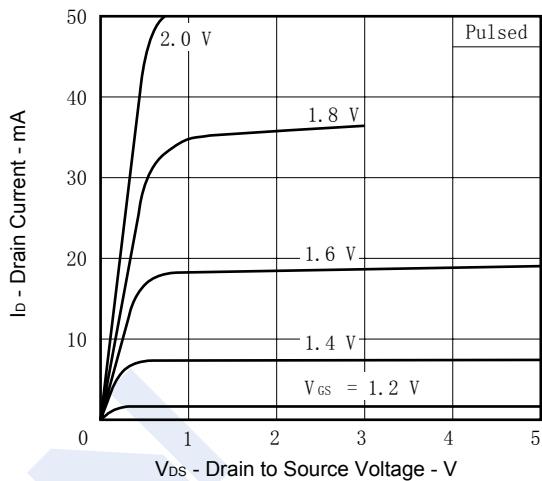
TOTAL POWER DISSIPATION vs.
AMBIENT TEMPERATURE



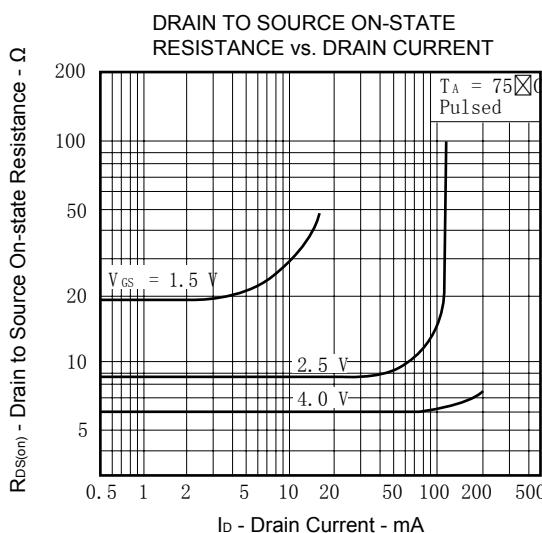
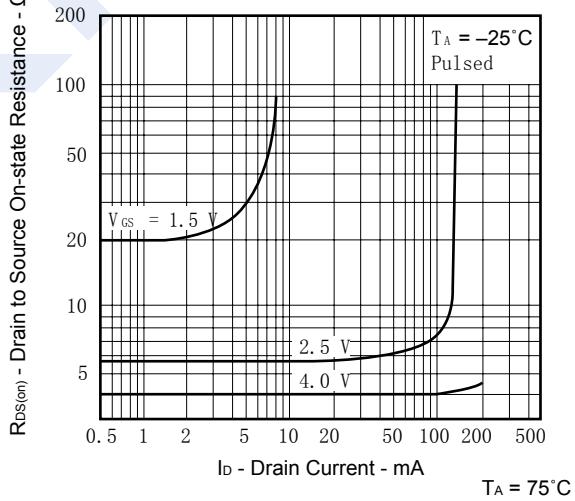
FORWARD TRANSFER ADMITTANCE vs.
DRAIN CURRENT



DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE



DRAIN TO SOURCE ON-STATE
RESISTANCE vs. DRAIN CURRENT



N-Channel MOSFET

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■ Typical Characteristics

